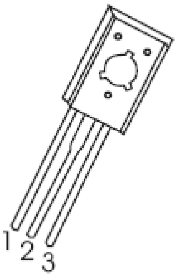
JCST

JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-126 Plastic-Encapsulate Transistors

TO-126

1. EMITTER
2. COLLECTOR
3. BASE



D882 TRANSISTOR (NPN)

FEATURES

- Power Dissipation

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	3	A
P_C	Collector Power Dissipation	1.25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25 ℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C = 100μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C = 10mA, I_B=0	30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}= 40 V, I_E=0			1	μA
Collector cut-off current	I_{CEO}	V_{CE}= 30 V, I_B=0			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 6 V, I_C=0			1	μA
DC current gain	h_{FE}	V_{CE}= 2 V, I_C= 1A	60		400	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C= 2A, I_B= 0.2 A			0.5	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C= 2A, I_B= 0.2 A			1.5	V
Transition frequency	f_T	V_{CE}= 5V, I_C=0.1A f =10MHz		90		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

B,Mar,2012

Typical Characteristics D882